

N-channel TrenchMOS standard level FET

5 October 2012

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

1.3 Applications

- 12V, 24V and 48V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

| Table 1. Qui | ck reference data | | | | | |
|-------------------|----------------------------------|--|-----|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | - | 100 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u> | - | - | 72 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | - | - | 182 | W |
| Static charact | eristics | 1 | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 20 A; T _j = 25 °C; Fig. 11 | - | 10.2 | 13 | mΩ |
| Dynamic char | acteristics | 1 | | | | |
| Q _{GD} | gate-drain charge | V_{GS} = 10 V; I _D = 20 A; V _{DS} = 80 V; T _j = 25 °C; <u>Fig. 13; Fig. 14</u> | - | 25.4 | 35.6 | nC |

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2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | mb | D |
| 2 | D | drain | | |
| 3 | S | source | | G-UF4 |
| mb | D | mounting base; connected to drain | D2PAK (SOT404) | mbb076 S |

3. Ordering information

| Table 3. Ordering information | | | | | |
|-----------------------------------|---------|--|---------|--|--|
| Type number | Package | | | | |
| | Name | Description | Version | | |
| BUK7613-100E | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 | | |

4. Marking

| Table 4. Marking codes | |
|------------------------|--------------|
| Type number | Marking code |
| BUK7613-100E | BUK7613-100E |

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|--|---------|------------------|--------------------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 100 | V |
| V _{DGR} | drain-gate voltage | R _{GS} = 20 kΩ | - | 100 | V |
| V _{GS} | gate-source voltage | T _j ≤ 175 °C; DC | -20 | 20 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u> | - | 72 | А |
| | | T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u> | - | 51 | А |
| I _{DM} | peak drain current | T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4 | - | 288 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | - | 182 | W |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
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| Symbol | Parameter | Conditions | | Min | Мах | Unit |
|----------------------|---|---|--------|-----|-----|------|
| Source-drain | Source-drain diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | | - | 72 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$ | | - | 288 | А |
| Avalanche ruggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $\label{eq:ld} \begin{array}{l} I_D = 72 \text{ A}; \ V_{sup} \leq 100 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped; \\ \hline Fig. \ 3 \end{array}$ | [1][2] | - | 121 | mJ |

Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
Refer to application note AN10273 for further information.

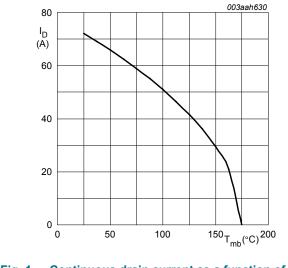


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$

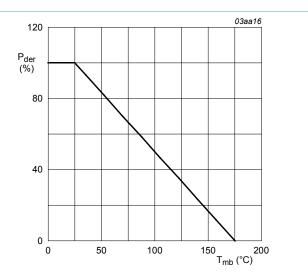
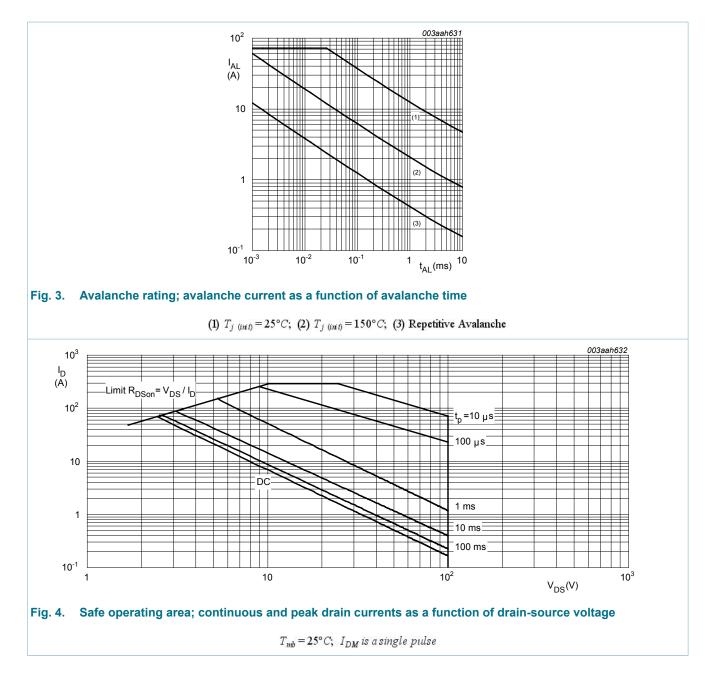


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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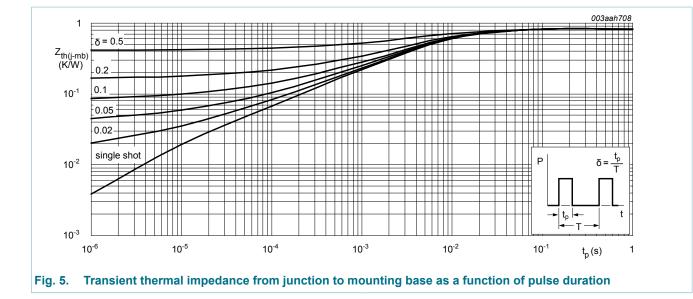


6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|--|-----|-----|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. <u>5</u> | - | - | 0.82 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | minimum footprint ; mounted on a printed-circuit board | - | 50 | - | K/W |

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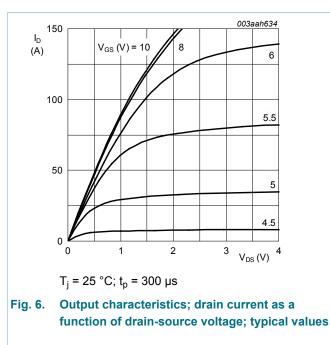


Characteristics 7.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---|-------------------------------|---|------|------|------|------|
| Static chara | acteristics | · · · | | | | |
| V _{(BR)DSS} | drain-source | I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C | 100 | - | - | V |
| | breakdown voltage | I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C | 90 | - | - | V |
| V _{GS(th)} gate-source t voltage | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10 | 2.4 | 3 | 4 | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 9 | 1 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9 | - | - | 4.5 | V |
| I _{DSS} | drain leakage current | V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C | - | 0.06 | 1 | μA |
| | | V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C | - | - | 500 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 100 | nA |
| | | V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} drain-source on-state resistance | | V _{GS} = 10 V; I _D = 20 A; T _j = 25 °C; Fig. 11 | - | 10.2 | 13 | mΩ |
| | | V _{GS} = 10 V; I _D = 20 A; T _j = 175 °C; Fig. 11; Fig. 12 | - | - | 35.1 | mΩ |
| R _G | gate resistance | f = 1 MHz | 0.48 | 0.96 | 1.92 | Ω |
| Dynamic cł | naracteristics | | I | | | |
| Q _{G(tot)} | total gate charge | I_D = 20 A; V_{DS} = 80 V; V_{GS} = 10 V; | - | 69.4 | 97.2 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C; <u>Fig. 13; Fig. 14</u> | - | 15.5 | 21.7 | nC |

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| Symbol | Parameter | Conditions | Mir | Тур | Max | Unit |
|---------------------|------------------------------|---|-----|------|-------|------|
| Q _{GD} | gate-drain charge | | - | 25.4 | 35.6 | nC |
| C _{iss} | input capacitance | V _{GS} = 0 V; V _{DS} = 20 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u> | - | 3400 | 4533 | pF |
| C _{oss} | output capacitance | V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; | - | 327 | 392 | pF |
| C _{rss} | reverse transfer capacitance | T _j = 25 °C; <u>Fig. 15</u> | - | 225 | 308 | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 80 V; R_L = 4 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω | - | 17.5 | 26.3 | ns |
| t _r | rise time | | - | 34 | 51 | ns |
| t _{d(off)} | turn-off delay time | | - | 44.8 | 67.2 | ns |
| t _f | fall time | | - | 34.1 | 51.2 | ns |
| L _D | internal drain inductance | from upper edge of mounting base to centre of die | - | 2.5 | - | nH |
| L _S | internal source inductance | measured from source lead to source bond pad ; T_j = 25 °C | - | 7.5 | - | nH |
| Source-dra | in diode | | | I | | |
| V _{SD} | source-drain voltage | I_{S} = 20 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u> | - | 0.83 | 1.2 | V |
| t _{rr} | reverse recovery time | I_{S} = 20 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V; | - | 48.8 | 63.4 | ns |
| Qr | recovered charge | V _{DS} = 25 V | - | 106 | 137.8 | nC |



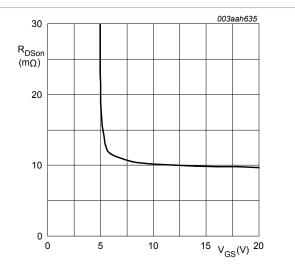
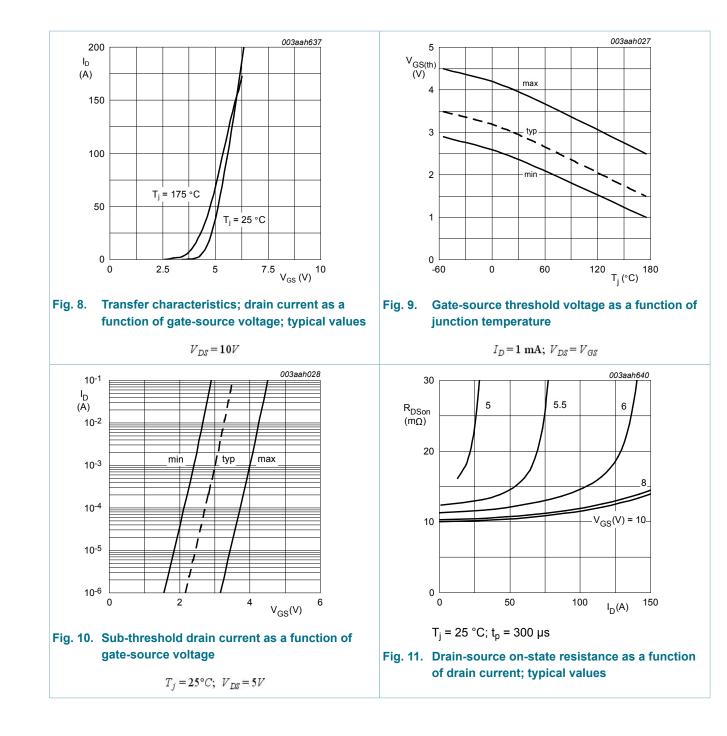


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 20A$

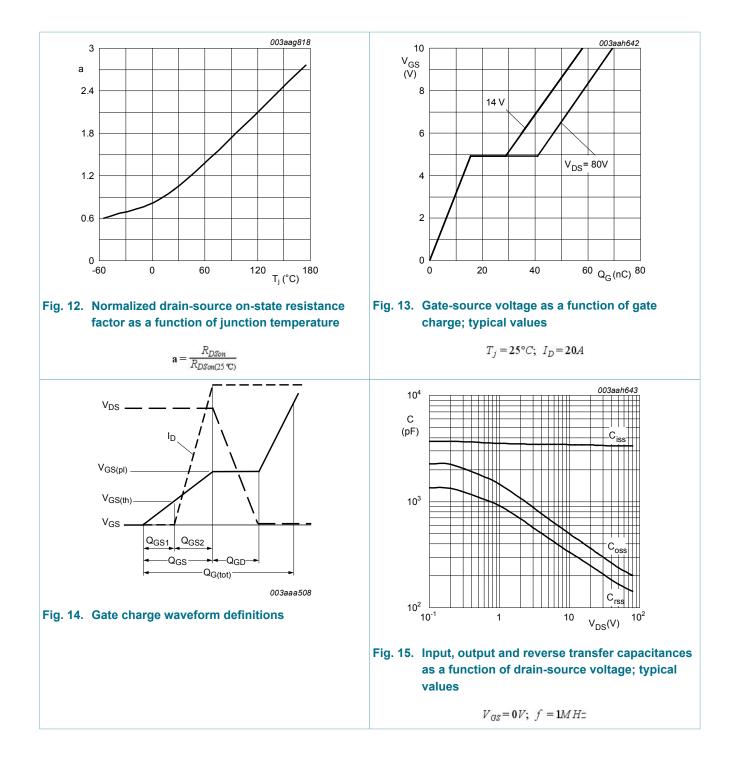
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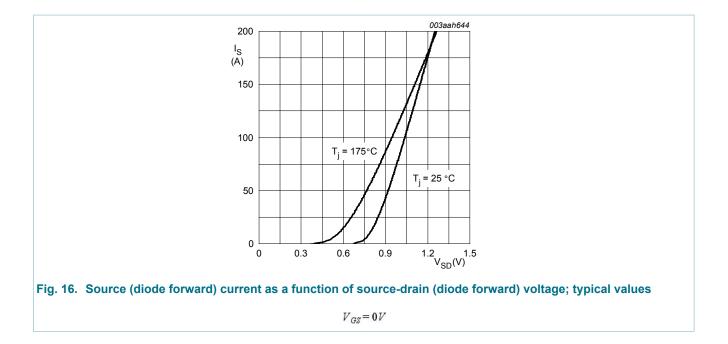
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8. Package outline

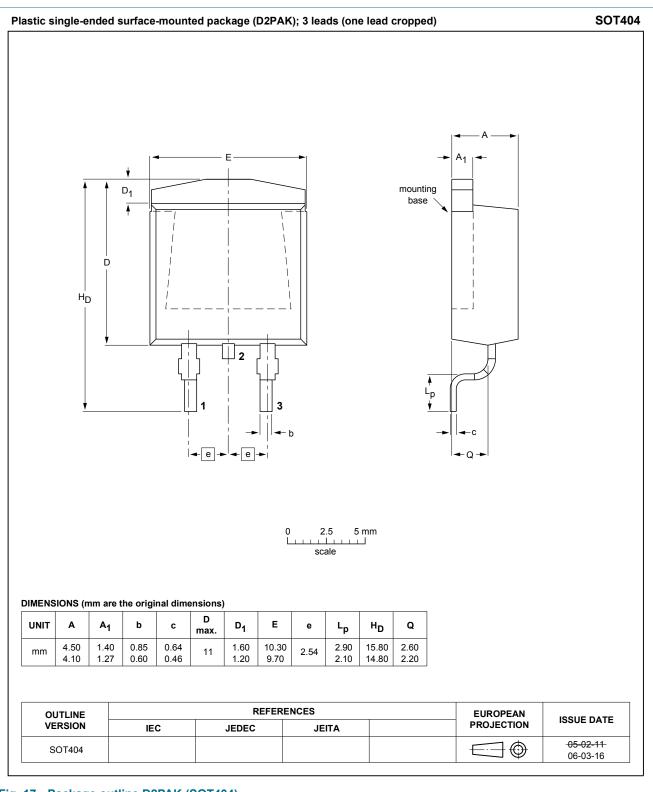


Fig. 17. Package outline D2PAK (SOT404)

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|--------------------------------------|-----------------------|---|
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